

1. Global joint venture starts operations as WeEn Semiconductors

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WeEn Semiconductors



Product data sheet

1. General description

Planar passivated very sensitive gate four quadrant triac in a SOT54 (TO-92) plastic package intended for use in applications requiring direct interfacing to logic ICs and low power gate drivers.

2. Features and benefits

- Direct interfacing to logic level ICs
- Direct interfacing to low power gate drive circuits
- High blocking voltage capability
- Planar passivated for voltage ruggedness and reliability
- Triggering in all four quadrants
- · Very sensitive gate in four quadrants

3. Applications

- General purpose low power motor control
- Home appliances
- Industrial process control
- Low power AC Fan controllers

4. Quick reference data

Table 1. Quick reference data

Symbol	Parameter	Conditions	Min	Тур	Max	Unit
V_{DRM}	repetitive peak off- state voltage		-	-	600	V
I _{TSM}	non-repetitive peak on- state current	full sine wave; $T_{j(init)} = 25 \text{ °C}$; $t_p = 20 \text{ ms}$; Fig. 4; Fig. 5	-	-	8	Α
I _{T(RMS)}	RMS on-state current	full sine wave; T _{lead} ≤ 45 °C; <u>Fig. 1</u> ; <u>Fig. 2</u> ; <u>Fig. 3</u>	-	-	1	Α
Static charact	teristics					
I _{GT}	gate trigger current	$V_D = 12 \text{ V; } I_T = 0.1 \text{ A; } T2+ G+;$ $T_j = 25 \text{ °C; } Fig. 7$	-	-	3	mA
		$V_D = 12 \text{ V}; I_T = 0.1 \text{ A}; T2+ G-;$ $T_j = 25 \text{ °C}; Fig. 7$	-	-	3	mA





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Symbol	Parameter	Conditions	Min	Тур	Max	Unit
		$V_D = 12 \text{ V}; I_T = 0.1 \text{ A}; \text{ T2- G-};$ $T_j = 25 \text{ °C}; \frac{\text{Fig. 7}}{\text{Fig. 7}}$	-	-	3	mA
		$V_D = 12 \text{ V; } I_T = 0.1 \text{ A; } T2- \text{ G+;}$ $T_j = 25 \text{ °C; } \frac{\text{Fig. 7}}{}$	-	-	5	mA

5. Pinning information

Table 2. Pinning information

Pin	Symbol	Description	Simplified outline	Graphic symbol
1	T2	main terminal 2		T2—T1
2	G	gate	<u> </u>	G sym051
3	T1	main terminal 1		
			TO-92 (SOT54)	

6. Ordering information

Table 3. Ordering information

Type number	Package					
	Name	Description	Version			
Z0103MA	TO-92	plastic single-ended leaded (through hole) package; 3 leads	SOT54			

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7. Limiting values

Table 4. Limiting values

In accordance with the Absolute Maximum Rating System (IEC 60134).

Symbol	Parameter	Conditions	Min	Max	Unit
V_{DRM}	repetitive peak off-state voltage		-	600	V
I _{T(RMS)}	RMS on-state current	full sine wave; T _{lead} ≤ 45 °C; <u>Fig. 1</u> ; Fig. 2; Fig. 3	-	1	A
I _{TSM}	non-repetitive peak on-state current	full sine wave; $T_{j(init)} = 25 \text{ °C}$; $t_p = 20 \text{ ms}$; Fig. 4; Fig. 5	-	8	A
		full sine wave; $T_{j(init)} = 25 ^{\circ}C$; $t_p = 16.7 ms$	-	8.5	A
l ² t	I2t for fusing	t _p = 10 ms; SIN	-	0.32	A ² s
dl _T /dt	rate of rise of on-state current	I _G = 6 mA; T2+ G+	-	50	A/µs
		I _G = 6 mA; T2+ G-	-	50	A/µs
		I _G = 10 mA; T2- G+	-	20	A/µs
		I _G = 6 mA; T2- G-	-	50	A/µs
I _{GM}	peak gate current		-	1	Α
P_GM	peak gate power		-	2	W
P _{G(AV)}	average gate power	over any 20 ms period	-	0.1	W
T _{stg}	storage temperature		-40	150	°C
Tj	junction temperature		-	125	°C

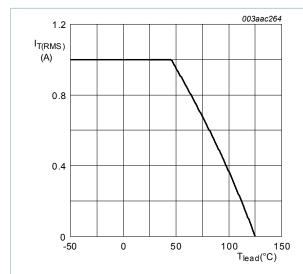
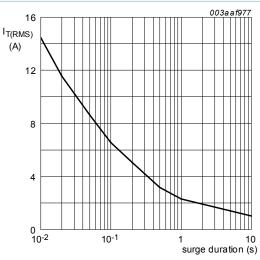


Fig. 1. RMS on-state current as a function of lead temperature; maximum values



f = 50 Hz; $T_{lead} = 45 ^{\circ}\text{C}$

Fig. 2. RMS on-state current as a function of surge duration; maximum values

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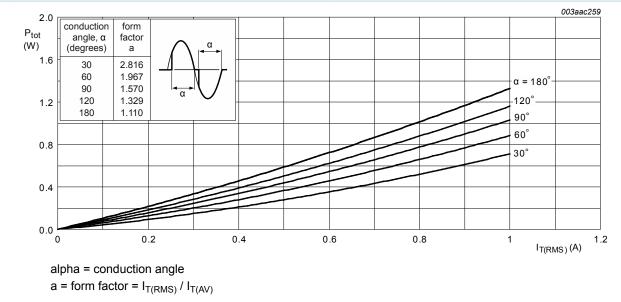


Fig. 3. Total power dissipation as a function of RMS on-state current; maximum values

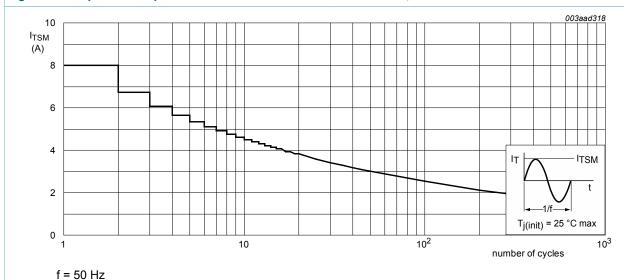
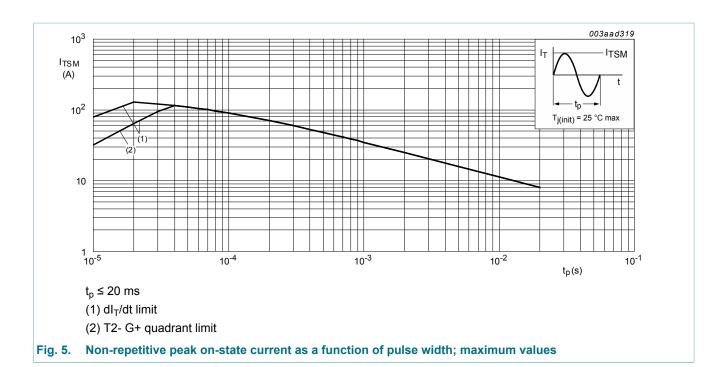


Fig. 4. Non-repetitive peak on-state current as a function of the number of sinusoidal current cycles; maximum values

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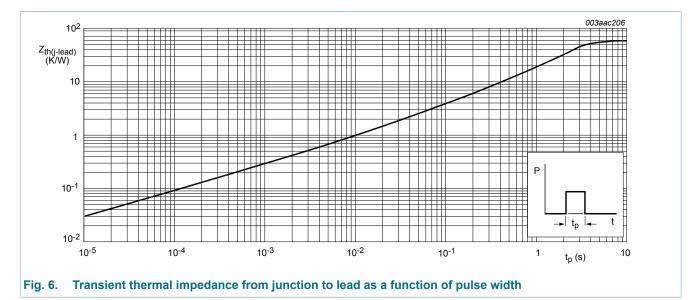


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8. Thermal characteristics

Table 5. Thermal characteristics

Symbol	Parameter	Conditions	Min	Тур	Max	Unit
R _{th(j-lead)}	thermal resistance from junction to lead	full cycle; Fig. 6	-	-	60	K/W
R _{th(j-a)}	thermal resistance from junction to ambient	full cycle; printed circuit board mounted; lead length = 4 mm	-	150	-	K/W



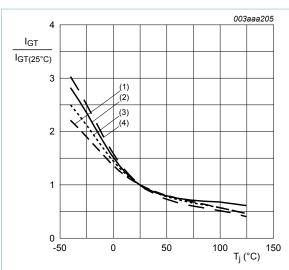
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9. Characteristics

Table 6. Characteristics

Symbol	Parameter	Conditions	Min	Тур	Max	Unit
Static chara	acteristics		'			
I _{GT}	gate trigger current	$V_D = 12 \text{ V}; I_T = 0.1 \text{ A}; T2+ G+;$ $T_j = 25 \text{ °C}; Fig. 7$	-	-	3	mA
		$V_D = 12 \text{ V}; I_T = 0.1 \text{ A}; T2+ \text{ G-};$ $T_j = 25 \text{ °C}; Fig. 7$	-	-	3	mA
		$V_D = 12 \text{ V}; I_T = 0.1 \text{ A}; \text{ T2- G-};$ $T_j = 25 \text{ °C}; \underline{\text{Fig. 7}}$	-	-	3	mA
		$V_D = 12 \text{ V}; I_T = 0.1 \text{ A}; \text{ T2- G+};$ $T_j = 25 \text{ °C}; \underline{\text{Fig. 7}}$	-	-	5	mA
l _L	latching current	$V_D = 12 \text{ V}; I_G = 0.1 \text{ A}; T2+ G+;$ $T_j = 25 \text{ °C}; Fig. 8$	-	-	7	mA
		$V_D = 12 \text{ V}; I_G = 0.1 \text{ A}; T2+ G-;$ $T_j = 25 \text{ °C}; Fig. 8$	-	-	15	mA
		$V_D = 12 \text{ V}; I_G = 0.1 \text{ A}; T2- G-;$ $T_j = 25 \text{ °C}; Fig. 8$	-	-	7	mA
		$V_D = 12 \text{ V; } I_G = 0.1 \text{ A; T2- G+;}$ $T_j = 25 \text{ °C; } Fig. 8$	-	-	7	mA
Н	holding current	V _D = 12 V; T _j = 25 °C; <u>Fig. 9</u>	-	-	7	mA
V _T	on-state voltage	I _T = 1.4 A; T _j = 25 °C; <u>Fig. 10</u>	-	1.3	1.6	V
V_{GT}	gate trigger voltage	$V_D = 12 \text{ V}; I_T = 0.1 \text{ A}; T_j = 25 \text{ °C};$ Fig. 11	-	-	1	V
		V _D = 600 V; I _T = 0.1 A; T _j = 125 °C; Fig. 11	0.2	-	-	V
D	off-state current	V _D = 600 V; T _j = 125 °C	-	-	0.5	mA
Dynamic ch	naracteristics					
dV _D /dt	rate of rise of off-state voltage	V_{DM} = 402 V; T_j = 110 °C; (V_{DM} = 67% of V_{DRM}); exponential waveform; gate open circuit; Fig. 12	10	-	-	V/µs
dV _{com} /dt	rate of change of commutating voltage	V_D = 400 V; T_j = 110 °C; $dI_{com}/$ dt = 0.44 A/ms; I_T = 1 A; gate open circuit	0.5	-	-	V/µs

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- (1) T2- G+
- (2) T2- G-
- (3) T2+ G-
- (4) T2+ G+

Fig. 7. Normalized gate trigger current as a function of junction temperature

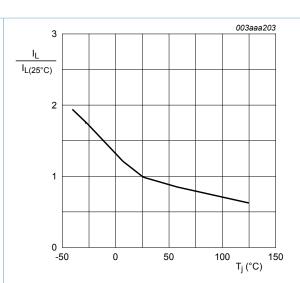


Fig. 8. Normalized latching current as a function of junction temperature

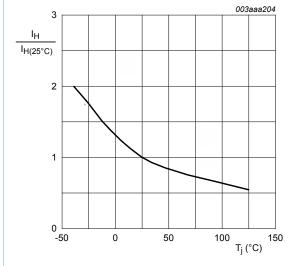
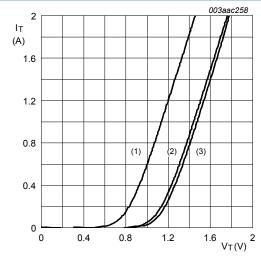


Fig. 9. Normalized holding current as a function of junction temperature



 $V_0 = 1.13 \text{ V}$

 $R_s = 0.31 \Omega$

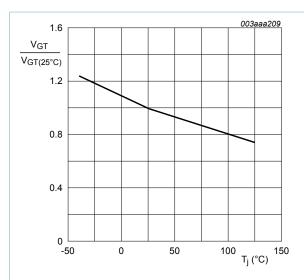
(1) T_i = 125 °C; typical values

(2) T_i = 125 °C; maximum values

(3) T_j = 25 °C; maximum values

Fig. 10. On-state current as a function of on-state voltage

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junction temperature

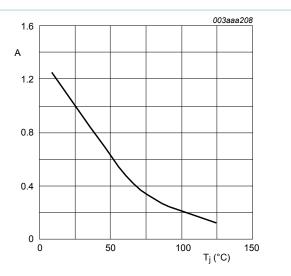


Fig. 11. Normalized gate trigger voltage as a function of Fig. 12. Normalized critical rate of rise of off-state voltage as a function of junction temperature; typical values

$$A = \frac{d\mathrm{V}_{D(Tj\,^{\circ}\,C)}\,/\,\,dt}{d\mathrm{V}_{D(25\,^{\circ}\,C)}/\,\,dt}$$

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10. Package outline

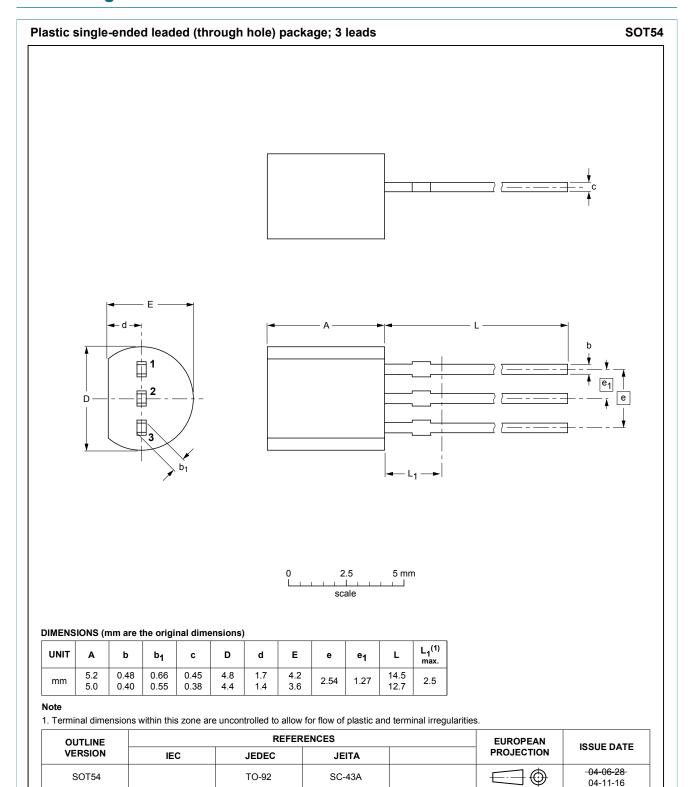


Fig. 13. Package outline TO-92 (SOT54)

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Objective [short] data sheet	Development	This document contains data from the objective specification for product development.
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